Product data sheet

1. General description

Hyperfast, epitaxial rectifier diode in a SOD113 (TO-220F) plastic package.

2. Features and benefits

- · Extremely fast switching
- Low thermal resistance
- · Low reverse recovery current
- Isolated package
- · Reduces switching loss in associated MOSFET

3. Applications

- Half-bridge or full-bridge switched-mode power supplies
- Continuous Current Mode (CCM) Power Factor Correction (PFC)
- Half-bridge lighting ballasts

4. Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions		Val	ues		Unit
Absolute	maximum rating						
V_{RRM}	repetitive peak reverse voltage		600			V	
$I_{F(AV)}$	average forward current	$δ = 0.5$; square-wave pulse; $T_h \le 37$ °C; Fig. 1; Fig. 2	10			А	
I _{FRM}	repetitive peak forward current	δ = 0.5 ; t_p = 25 μs; $T_h \le$ 37 °C; square-wave pulse	20		Α		
	non-repetitive peak	t _p = 10 ms; T _{j(init)} = 25 °C; sine-wave pulse	91			Α	
forward current		t_p = 8.3 ms; $T_{j(init)}$ = 25 °C; sine-wave pulse	100			Α	
Symbol	Parameter	Conditions	Min Typ Max		Max	Unit	
Static ch	aracteristics						
V _F	forward voltage	I _F = 10 A; T _j = 25 °C; <u>Fig. 4</u>	-		1.89	2.9	V
		I _F = 10 A; T _j = 150 °C; <u>Fig. 4</u>	-		1.32	2.03	V
		I _F = 20 A; T _j = 150 °C; <u>Fig. 4</u>	-		1.64	2.34	V
Dynamic	characteristics		1		1		1
t _{rr}	reverse recovery time	$I_F = 1 \text{ A}; V_R = 30 \text{ V}; dI_F/dt = 50 \text{ A}/\mu\text{s};$ $T_i = 25 \text{ °C}; Fig. 5$	-		35	55	ns

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5. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	K	cathode	mb	
2	А	anode		K — A
mb	n.c.	mounting base; isolated	1 2 SOD113 (2-lead TO-220F)	001aaa020

6. Ordering information

Table 3. Ordering information

Type number	Package	Package				
	Name	Description	Version			
BYC10X-600	TO-220F	plastic single-ended package; isolated heatsink mounted; 1 mounting hole; 2-lead TO-220 "full pack"	SOD113			

7. Marking

Table 4. Marking codes

Type number	Marking codes
BYC10X-600	BYC10X-600

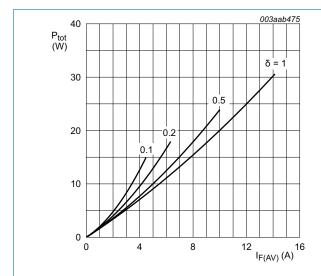
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8. Limiting values

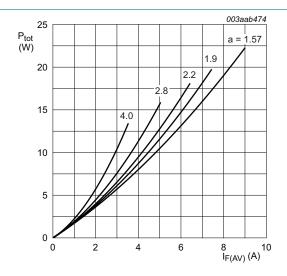
Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Parameter	Conditions	Values	Unit
repetitive peak reverse voltage		600	V
crest working reverse voltage		600	V
reverse voltage	δ = 1.0 ; square-wave pulse; T _h ≤ 100 °C;	500	V
average forward current	$δ = 0.5$; square-wave pulse; $T_h \le 37$ °C; Fig. 1; Fig. 2	10	А
repetitive peak forward current	$δ = 0.5$; $t_p = 25 \mu s$; $T_h \le 37 °C$; square-wave pulse	20	А
non-repetitive peak	t_p = 10 ms; $T_{j(init)}$ = 25 °C; sine-wave pulse	91	А
forward current	t_p = 8.3 ms; $T_{j(init)}$ = 25 °C; sine-wave pulse	100	А
storage temperature		-40 to 150	°C
junction temperature		150	°C
	repetitive peak reverse voltage crest working reverse voltage reverse voltage average forward current repetitive peak forward current non-repetitive peak forward current storage temperature	$ \begin{array}{c} \text{repetitive peak reverse} \\ \text{voltage} \\ \\ \text{crest working reverse} \\ \text{voltage} \\ \\ \text{reverse voltage} \\ \\ \text{average forward current} \\ \\ \text{superage forward current} \\ \\ superage$	$\begin{array}{c} \text{repetitive peak reverse} \\ \text{voltage} \\ \\ \text{crest working reverse} \\ \text{voltage} \\ \\ \text{reverse voltage} \\ \\ \text{average forward current} \\ \\ \text{definition} \\ \\ \\ \text{definition} \\ \\ \text{definition} \\ \\ \\ \text{definition} \\ \\ \\ \text{definition} \\ \\ \\ \text$



 $I_{\text{F(AV)}} = I_{\text{F(RMS)}} \times \sqrt{\delta}$ Fig. 1. Forward power dissipation as a function of average forward current; square waveform; maximum values



a = form factor = I_{F(RMS)}/I_{F(AV)}
 Fig. 2. Forward power dissipation as a function of average forward current; sinusoidal waveform; maximum values

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9. Thermal characteristics

Table 6. Thermal characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
R _{th(j-h)} thermal resistance		with heatsink compound; Fig 3	-	-	4.8	K/W
,	from junction to heatsink	without heatsink compound	-	-	5.9	K/W
R _{th(j-a)}	thermal resistance from junction to ambient free air	in free air	-	60	-	K/W

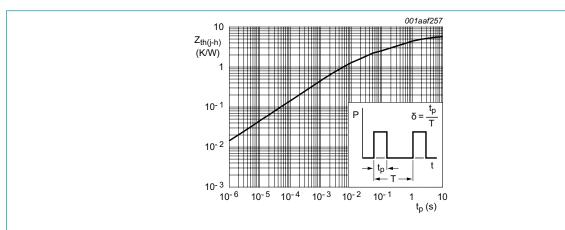


Fig. 3. Transient thermal impedance from junction to heatsink as a function of pulse duration

10. Isolation characteristics

Table 7. Isolation characteristics

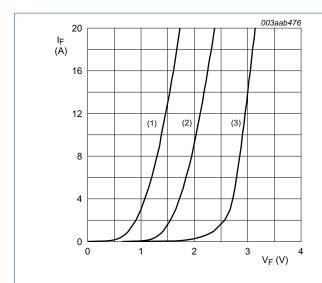
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V _{isol(RMS)}	RMS isolation voltage	50 Hz ≤ f ≤ 60 Hz; RH ≤ 65 %; from all pins to external heatsink; sinusoidal waveform; clean and dust free	-	-	2500	V
C_{isol}	isolation capacitance	from cathode to external heatsink; f = 1 MHz	-	10	-	PF

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11. Characteristics

Table 8 Characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static cha	racteristics					
V _F	forward voltage	I _F = 10 A; T _j = 25 °C; <u>Fig. 4</u>	-	1.89	2.9	V
		I _F = 10 A; T _j = 150 °C; <u>Fig. 4</u>	-	1.32	2.03	V
		I _F = 20 A; T _j = 150 °C; <u>Fig. 4</u>	-	1.64	2.34	V
I _R	reverse current	V _R = 600 V; T _j = 25 °C	-	9	200	μΑ
		V _R = 500 V; T _j = 100 °C	-	1.1	3	mA
Dynamic	characteristics			1	1	1
t _{rr} reverse rec	reverse recovery time	$I_F = 1 \text{ A; } V_R = 30 \text{ V; } dI_F/dt = 50 \text{ A/}\mu\text{s;}$ $T_j = 25 \text{ °C; } \frac{\text{Fig. 5}}{}$	-	35	55	ns
		$I_F = 10 \text{ A}; V_R = 400 \text{ V}; dI_F/dt = 500 \text{ A/}\mu\text{s};$ $T_j = 25 \text{ °C}; Fig. 5$		19	-	ns
		$I_F = 10 \text{ A}; V_R = 400 \text{ V}; dI_F/dt = 500 \text{ A/}\mu\text{s};$ $T_j = 100 \text{ °C}; Fig. 5$	-	32	40	ns
I _{RM} peak reverse recovery current		$I_F = 10 \text{ A}; V_R = 400 \text{ V}; dI_F/dt = 500 \text{ A/}\mu\text{s};$ $T_j = 100 \text{ °C}; Fig. 5$	-	9.5	12	А
		$I_F = 10 \text{ A}; V_R = 400 \text{ V}; dI_F/dt = 50 \text{ A/}\mu\text{s};$ $T_j = 125 \text{ °C}; Fig. 5$	-	3	7.5	А
V_{FR}	forward recovery voltage	$I_F = 10 \text{ A}; \text{ dI}_F/\text{dt} = 100 \text{ A/}\mu\text{s};$ $T_i = 25 \text{ °C}; \frac{\text{Fig. 6}}{100 \text{ A}}$	-	8	11	V



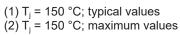


Fig. 4. Forward current as a function of forward voltage

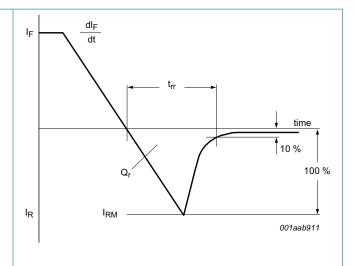
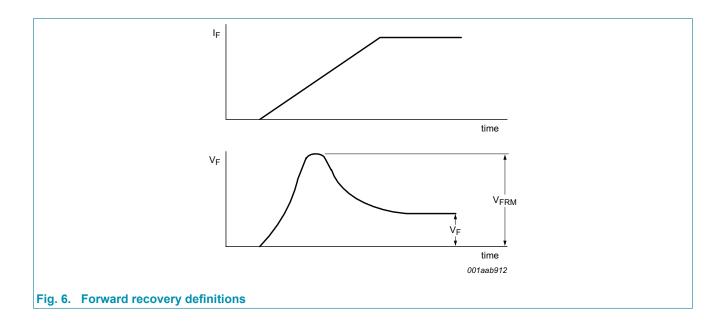


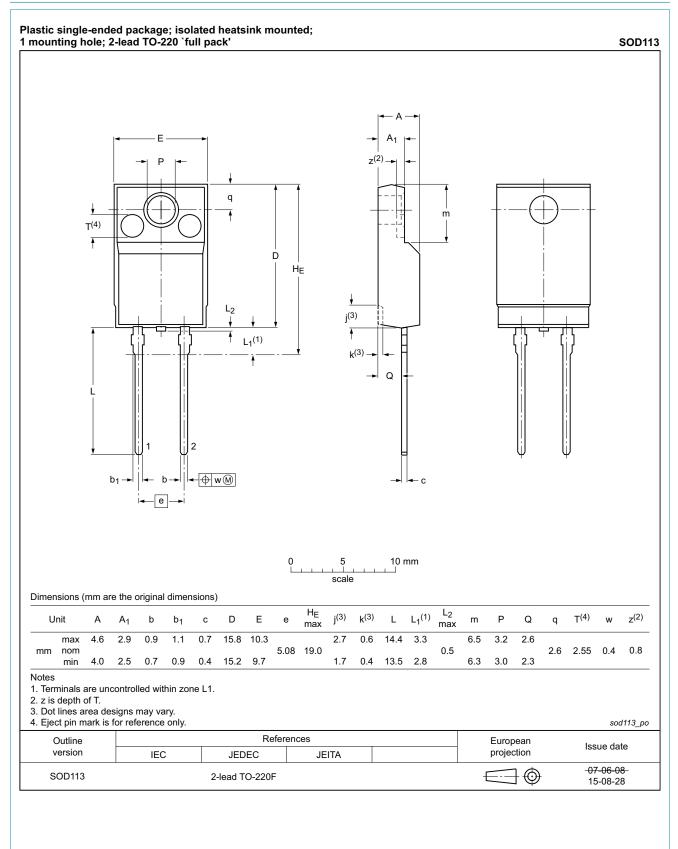
Fig. 5. Reverse recovery definitions; ramp recovery

⁽³⁾ T_i = 25 °C; maximum values

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12. Package outline



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13. Revision history

Table 9. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes			
BYC10X-600 v.3	20180926	Product data sheet	-	BYC10X-600_2			
Modifications:	Change from NXP version to WeEn version						
BYC10X-600_2	20080116	Product data sheet	-	BYC10X-600_1			
Modifications:	"Limiting values", I _{F(AV)} and I _{FRM} conditions for T _h changed to 37 °C.						
BYC10X-600_1	20070831	Product data sheet	-	-			

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14. Legal information

Data sheet status

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

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